A FERROELECTRIC CAPACITOR HAVING AN OXIDE ELECTRODE TEMPLATE AND A METHOD OF MANUFACTURE THEREFOR

ABSTRACT OF THE DISCLOSURE

The present invention provides a ferroelectric capacitor, a method for manufacture therefor, and a ferroelectric random access memory (FeRAM) device. The ferroelectric capacitor (100), among other elements, may include a first electrode layer (162) located over a substrate (110), wherein the first electrode layer (162) includes iridium, and an oxide electrode template (164) located over the first electrode layer (162). The ferroelectric capacitor (100) may further include a ferroelectric dielectric layer (165) located over the oxide electrode template (164), and a second electrode layer (170) located over the ferroelectric dielectric layer (165).